

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions, and listings, of claims in this application.

1. (Currently Amended) A pulse generator comprising a plurality of unit cells, wherein an n^{th} unit cell (n is a natural number more than 2) generates a pulse in response to a divided-by- N clock signal (N is a natural number), a signal output from an $(n-1)^{\text{th}}$ unit cell and a signal output from an $(n+1)^{\text{th}}$ unit cell, wherein the pulse is a gated version of the divided-by- N clock signal.

2. (Original) The pulse generator of claim 1, wherein the n^{th} unit cell is reset or generates the pulse, the width of the pulse being equivalent to the width of the divided-by- N clock signal, based on the logic level of the signal output from the $(n-1)^{\text{th}}$ unit cell and the logic level of the signal output from the $(n+1)^{\text{th}}$ unit cell.

3. (Original) The pulse generator of claim 1, wherein phases of the signal output from the $(n-1)^{\text{th}}$ unit cell and the signal output from the $(n+1)^{\text{th}}$ unit cell are changed with a time difference.

4. (Original) The pulse generator of claim 1, wherein the n^{th} unit cell comprises:
a first NAND gate that NANDs the signal output from the $(n-1)^{\text{th}}$ unit cell and the signal output from the $(n+1)^{\text{th}}$ unit cell;

a first inverter that inverts a signal output from the first NAND gate;

a second NAND gate that NANDs the divided-by- N clock signal and a signal output from the first inverter;

a second inverter that inverts a signal output from the second NAND gate and outputs the pulse as an inverted signal; and

a latch that latches a reset signal and the signal output from the second NAND gate.

5. (Original) The pulse generator of claim 4, wherein the second NAND gate comprises:

first and second positive metal oxide semiconductor (PMOS) transistors; and

first and second negative metal oxide semiconductor (NMOS) transistors,

wherein the divided-by-N clock signal is input to a gate of the first PMOS transistor and a gate of the first NMOS transistor, and a signal output from the first inverter is input to a gate of the second PMOS transistor and a gate of the second NMOS transistor.

6. (Currently Amended) A pulse generator comprising a plurality of unit cells,

wherein a divided-by-N clock signal (N is a natural number), a signal output from a second output terminal of an $n-1^{\text{th}}$ unit cell (n is a natural number more than 2), and a signal output from a third output terminal of an $n+1^{\text{th}}$ unit cell are input to a first input terminal, a second input terminal, and a third input terminal of an n^{th} unit cell of the plurality of unit cells,

wherein the n^{th} unit cell outputs a pulse whose width is equivalent to the width of the divided-by-N clock signal to a first output terminal of the n^{th} unit cell in response to the signals that are input to the first, second and third input terminals of the n^{th} unit cell, wherein the pulse is a gated version of the divided-by-N clock signal.

7. (Original) The pulse generator of claim 6, wherein the n^{th} unit cell is reset or outputs the pulse whose width is equivalent to the width of the divided-by-N clock signal

to the first output terminal of the n^{th} unit cell, based on the logic level of the signal output from the third output terminal of the $(n+1)^{\text{th}}$ unit cell.

8. (Original) The pulse generator of claim 6, wherein phases of the signal output from the second output terminal of the $n-1^{\text{th}}$ unit cell and the signal output from the third output terminal of the $n+1^{\text{th}}$ unit cell are changed with a time difference.

9. (Original) The pulse generator of claim 6, wherein the n^{th} unit cell comprises:

a first NAND gate that NANDs the signal which is output from the $n-1^{\text{th}}$ unit cell and input to the second input terminal of the n^{th} unit cell, and the signal which is output from the $n+1^{\text{th}}$ unit cell and input to the third input terminal of the n^{th} unit cell;

a first inverter that inverts a signal output from the first NAND gate;

a second NAND gate that NANDs the divided-by-N clock signal input to the first input terminal of the n^{th} unit cell and a signal output from the first inverter;

a second inverter that inverts a signal output from the second NAND gate and outputs an inverted signal as the output signal of the n^{th} unit cell; and

a latch that latches a reset signal, and a signal output from the second NAND gate.

10. (Original) The pulse generator of claim 9, wherein the second NAND gate comprises:

first and second PMOS transistors; and

first and second NMOS transistors,

wherein the divided-by-N clock signal is input to a gate of the first PMOS transistor and a gate of the first NMOS transistor, and the signal output from the first inverter is input to a gate of the second PMOS transistor and a gate of the second NMOS transistor.

11. (Original) The pulse generator of claim 6, wherein the n^{th} unit cell comprises:

a first NAND gate that NANDs the signal which is output from the $n-1^{\text{th}}$ unit cell and input via the second input terminal of the n^{th} unit cell, and the signal which is output from the $n+1^{\text{th}}$ unit cell and input via the third input terminal of the n^{th} unit cell;

a first inverter that inverts a signal output from the first NAND gate;

a second NAND gate that NANDs the divided-by-N clock signal input via the first input terminal of the n^{th} unit cell and a signal output from the first inverter;

a second inverter that inverts a signal output from the second NAND gate and outputs an inverted signal as an output signal of the n^{th} unit cell;

a first transmission circuit that responds to the signal output from the second NAND gate and the signal output from the second inverter;

a second transmission circuit that responds to the signal output from the second NAND gate and the signal output from the second inverter;

a third NAND gate that NANDs a reset signal and a signal output from the shared node and outputs the result of NAND to the third output terminal of the n^{th} unit cell; and

a third inverter that inverts the signal output from the third NAND gate and outputs an inverted signal to the second output terminal of the n^{th} unit cell.

12. (Original) The pulse generator of claim 11, wherein the second NAND gate comprises:

first and second PMOS transistors; and

first and second NMOS transistors,

wherein the divided-by-N clock signal input to the first input terminal of the n^{th} unit cell is input to a gate of the first PMOS transistor and a gate of the first NMOS

transistor, and the signal output from the second inverter is input to a gate of the second PMOS transistor and a gate of the second NMOS transistor.

13-18. (Canceled)